

ABSTRACT

To provide an Al bonding wire exhibiting a favorable high-temperature and high-humidity service life in a high-temperature and high-humidity environment required for next-generation vehicle-mounted power devices. The Al bonding wire for semiconductor devices containing equal to or larger than 3 mass ppm and equal to or smaller than 500 mass ppm of one or more of Pd and Pt in total, in which, as a result of measuring a crystal orientation on a cross section parallel to a wire axis direction including a wire axis of the bonding wire, an orientation ratio of a <100> crystal orientation angled at 15 degrees or less to the wire axis direction is equal to or higher than 30% and equal to or lower than 90%.

FIG. 1